

Nonequilibrium Noise in Metals at Mesoscopic Scales

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We review a semiclassical theory of high-field current noise in strongly degenerate conductors, based on propagator solutions to the Boltzmann transport equation for current fluctuations. The theory provides a microscopic description of correlation-induced suppression of noise in high-mobility heterojunction devices, and is also applicable to disordered mesoscopic structures. We discuss the behaviour of thermal noise in a mesoscopic wire, from equilibrium to the high-field limit.

Keywords: nonequilibrium fluctuations, noise, electron correlations, mesoscopics

Large departures from equilibrium are a major issue in transport theory,^{1,2} more so in the mesoscopic realm since, at nanometre scales, very modest external voltages easily generate intense driving fields with highly nonlinear effects.³ The problem is of greater severity for many-body properties such as current noise,^{4,5} and in this paper we study aspects of high-field current fluctuations for degenerate electrons, an area scarcely explored. We outline a microscopic approach to fluctuations in metallic systems far from equilibrium, illustrating this with an application to real heterojunction devices⁶ and finally with an analysis of high-field thermal noise in an idealised, disordered mesoscopic wire.⁷

I. FORMALISM

A. Transport

Our method generalises the purely classical Boltzmann-Green-function theory of Stanton and Wilkins.^{4,5,8} We start with the one-body transport equation. For simplicity consider a uniform conductor. The semiclassical one-electron Boltzmann equation is

$$\frac{\partial}{\partial t} f_{s;k}(t) = \frac{eE}{h} \frac{\partial}{\partial k} f_{s;k}(t) = C_{s;k}[f(t)]; \quad (1)$$

where the time-dependent distribution $f_{s;k}(t)$ is labelled by band-and-spin index s and wave vector k ; the local driving field (uniform here) is E . The collision operator $C_{s;k}[f]$ carries, at the semiclassical level, the effects of microscopic scattering from all sources. In a degenerate system, C is inherently nonlinear in f . Normalisation to the density n is such that $n = \sum_{s;k} f_{s;k} = 1$ in a system of volume V .

In the steady state, Eq. (1) maps the equilibrium Fermi-Dirac distribution f^{eq} to f . Introducing the difference function $g = f - f^{\text{eq}}$, we have

$$\frac{eE}{h} \frac{\partial g_{s;k}}{\partial k} = \frac{eE}{h} \frac{\partial f_{s;k}^{\text{eq}}}{\partial k} + C_{s;k}[f^{\text{eq}} + g]; \quad (2)$$

B. Steady-State Fluctuations

The equilibrium density-density fluctuation for free electrons is $f^{\text{eq}} = k_B T \partial f^{\text{eq}} / \partial \mu_F$, where $k_B T$ is the thermal energy and μ_F is the chemical potential. Eq. (2), linearised, maps f^{eq} adiabatically to its nonequilibrium counterpart. Solving for the fluctuation difference g according to

$$\frac{eE}{h} \frac{\partial g_{s;k}}{\partial k} = \frac{eE}{h} \frac{\partial f_{s;k}^{\text{eq}}}{\partial k} + \sum_{s^0;k^0} \frac{C_{s;k}}{f_{s^0;k^0}^{\text{eq}}} f_{s^0;k^0}^{\text{eq}} + g_{s^0;k^0}; \quad (3)$$

the complete steady-state fluctuation can be constructed as $f = f^{\text{eq}} + g$. The effect of degeneracy on g is explicit, since $f^{\text{eq}} = f^{\text{eq}}(1 - f^{\text{eq}})$. Moreover, the leading right-hand term of Eq. (2) for g itself contains $\partial f^{\text{eq}} / \partial k = 1 / f^{\text{eq}}$. Thus the very nature of the equilibrium state imposes a connection between the nonequilibrium one- and two-particle structures, g and f .⁹

C. Dynamic Fluctuations

These are obtained from the linearised form of Eq. (1) by calculating its retarded resolvent $R(t)$,¹⁰ with which one then constructs the transient current autocorrelation $C_{xx}(t)$:

$$R_{ss^0;kk^0}(t, t^0) = \frac{f_{s;k}(t) - f_{s^0;k^0}(t^0)}{f_{s^0;k^0}^{\text{eq}}(t^0)} \quad (4)$$

and

$$C_{xx}(t) = \frac{e^2}{l^2} \sum_{s,jk} \sum_{s^0,jk^0} (v_x)_{s,jk} R_{ss^0,jk^0}(t) \quad (5)$$

$$R_{ss^0,jk^0}(l) = (v_x)_{s^0,jk^0} f_{s^0,jk^0};$$

where $(v_x)_{s,jk}$ is the group velocity in the direction of E , and l is the sample length. Eq. (5) extends the classical definition of Stanton and Wilkins⁴ to degenerate systems, with the following interpretation. At $t = 0$ a spontaneous fluctuation $v_x^0 f^0$ perturbs the flux in its steady state. Its subsequent fate is determined by the propagator $R(t)$. After removal of the steady-state asymptote at $t \rightarrow 1$, the product $(v_x = l) R(v_x^0 = l) f^0$ gives the dynamical current-current correlation.

Our premise is that fluctuations in the electron gas are induced almost instantaneously compared with their relaxation rate. This allows a two-step calculation. First, compute the strength of the spontaneous fluctuations in the steady state (with the underlying equilibrium statistics included manifestly). Second, derive their semiclassical dynamics and hence the noise spectrum. This prescription satisfies the fluctuation-dissipation theorem.⁹

II. CONSEQUENCES

The simplest form of our theory is based on the Dnude model in a single parabolic conduction band, for which $C = G$; at room temperature the inelastic collision time is of order 10^{-13} s. The noise spectral density is^{4,6}

$$S(f) = \frac{1}{4} \int_0^1 C_{xx}(t) \cos(2\pi f t) dt$$

$$= \frac{4G k_B T}{1 + (2\pi f)^2} + \frac{n}{n} \frac{m^2 E^2}{k_B T}; \quad (6)$$

in which G is the sample conductance, m the effective mass, $e = m$ the mobility, and $n = 2 \sum_k f_k$. For $E = 0$ in the static limit, $S(0)$ is the Johnson-Nyquist noise. At high fields the "hot-electron" term E^2 in Eq. (6) is quite strongly suppressed by degeneracy; while a classical system has $n = 1$, a 1-dimensional degenerate system has, instead, $n = k_B T = 2T_F$.

Equations (3), (5), and (6) show S to be a linear functional of f^{eq} . Insofar as Coulomb and exchange interactions modify the free-particle form of the equilibrium density-density fluctuation, it follows that thermal noise carries a signature of the internal correlations of the electron gas. Apart from its physical significance, this has immediate practical implications.

A. Device Noise

An important consequence for microwave technology is reduction of thermal noise in a two-dimensional (2D)

electron gas,⁶ confined at the heterojunction of a high-electron-mobility transistor (HEMT).¹¹ Basically, the occupancy within a HEMT is $f_k^{\text{eq}} = f_1 + \exp[(\epsilon_k + \epsilon_0(n)) / k_B T]^{-1}$, where ϵ_k is the 2D band energy and $\epsilon_0(n)$ is the ground-state energy in the heterojunction quantum well. The density governs ϵ_0 because the mean-field electronic potential in the well is self-consistent. As a result f^{eq} is renormalised to f^{eq} by the suppression factor⁶ $(n) = [1 + (d\epsilon_0/dn) n / k_B T]^{-1}$.

The observable noise is therefore reduced by as much as 65% for sheet densities of 10^{12} cm^{-2} , typical in conductive channels. Under normal conditions this means that the effective noise temperature in a HEMT is 100K, not the 300K of a bulk conductor. Such suppression is unique to self-consistently quantised systems. Circuit-theoretical arguments show that, in production devices, it should lead to an extrinsic noise figure which is half that of bulk field-effect transistors, of otherwise similar circuit performance.⁶ This agrees well with real device comparisons.¹²

B. Mesoscopic Noise

Sample lengths approaching the mean free path take us into the mesoscopic regime.⁷ Even for an embedded slice of long, spatially uniform conductor, the propagator $R(t)$ acquires spatial structure below l , satisfying

$$\frac{\partial}{\partial t} + v_{s,jk} \frac{\partial}{\partial r} - \frac{eE}{h} \frac{\partial}{\partial k} R_{ss^0,jk^0}(r, r^0; t, t^0)$$

$$= -\sum_{k^0, s^0} (r, r^0)(t, t^0)$$

$$+ \sum_{s^0, jk^0} \frac{C_{s,jk}}{f_{s^0, jk^0}} R_{s^0 s^0, jk^0 k^0}(r, r^0; t, t^0); \quad (7)$$

The sums in Eq. (5) for C_{xx} now include integrals over the mesoscopic slice, while the macroscopically homogeneous propagator of Eq. (4) re-emerges as $\int dr R =$.

Using Eqs. (7), (5), and (6) we have computed the thermal-noise spectrum for an embedded uniform 1D wire, in the Dnude model previously studied by Stanton⁸ within the classical limit $k_B T \gg T_F$. The example, although suggestive, is artificial not least because "wire" and "leads" are operationally indistinguishable.

We examine the degenerate limit, for which $\epsilon = v_F$ in terms of the Fermi velocity. At zero frequency the equilibrium noise is given by

$$S^{\text{eq}}(0) = 4G k_B T \frac{1}{l} (1 - e^{-l/\lambda}) ; \quad (8)$$

where l is the length of the wire segment, much smaller than the enclosing 1D "volume". In the limit $l \rightarrow \infty$ Eq. (8) reduces to $S^{\text{eq}}(0) = (4e^2/h) k_B T$. Since this is the ballistic regime we note that the thermal noise scales with e^2/h , the universal unit of conductance.⁷

On the other hand the nonequilibrium ballistic noise is

$$S(0) = \frac{4e^2}{h} k_B T \left[1 + \frac{1}{1 + \frac{E}{v_F}} \exp\left(-\frac{2v_F}{E}\right) \right] : \quad (9)$$

The expression is nonperturbative in E owing to nonanalyticity of the solutions to Eqs. (2) and (3) for a uniform nonequilibrium system.^{3,8} Our exact, if simple, model calculation shows that one cannot take for granted the existence of an expansion for the fluctuations near the equilibrium state, in powers of the field.

At large fields the ballistic noise becomes linear:⁸

$$S(0) = \frac{4e^2}{h} k_B T \frac{E}{v_F} + O(E^2) \\ \approx 4G k_B T \frac{eV}{4V_F} ; \quad (10)$$

where $V = El$ is the voltage across the wire (still with $l \ll \lambda$), and we have reinstated the Johnson-Nyquist normalisation. Two remarks can be made on this equation:

(a) the linear dependence on E is kinematic, reflecting the shift of the centroid of the fluctuation distribution in k -space by $eE = \hbar$. In contrast, the quadratic dependence of the macroscopic noise in Eq. (6) is dissipative, and sensitive to thermal broadening of ϵ_k over the bulk.

(b) The second form of Eq. (10) is equivalent to $S(0) = 2eI(n=n)$, where $I = GV$ is the current through the wire. Thus, ballistic thermal noise in the 1D Drude approximation is given by the classical shot-noise formula^{7,8} attenuated by the degeneracy, a result valid for all densities and temperatures.

While thermal noise must go to zero with the temperature, this is not the case for true shot noise, whose non-thermal origin is the random transit of individual carriers across the sample. It is beyond our present scope to discuss applications of the Boltzmann-Green-function formalism to diffusive mesoscopic shot noise,^{7,13,14} which we are actively investigating.

III. SUMMARY

We have outlined a semiclassical framework for calculating thermal fluctuations in metallic electron systems far from equilibrium. Our approach also describes how Coulomb and exchange correlations, present at equilibrium, appear in the nonequilibrium current noise. The consequences for device design are exemplified by the physics of correlation-induced noise suppression in heterojunction field-effect transistors.

The same formalism can be applied to diffusive mesoscopic noise. An illustrative 1D model provides evidence that mesoscopic noise may not always have a perturbation expansion at low fields, if the underlying distributions are nonanalytic in the equilibrium limit. At high fields the model recovers the shot-noise-like behaviour of ballistic thermal noise.⁸ For a metallic wire we find that this is attenuated in proportion to the degeneracy of the system.

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